



Advanced Thermoelectric Materials for Radioisotope Thermoelectric Generators

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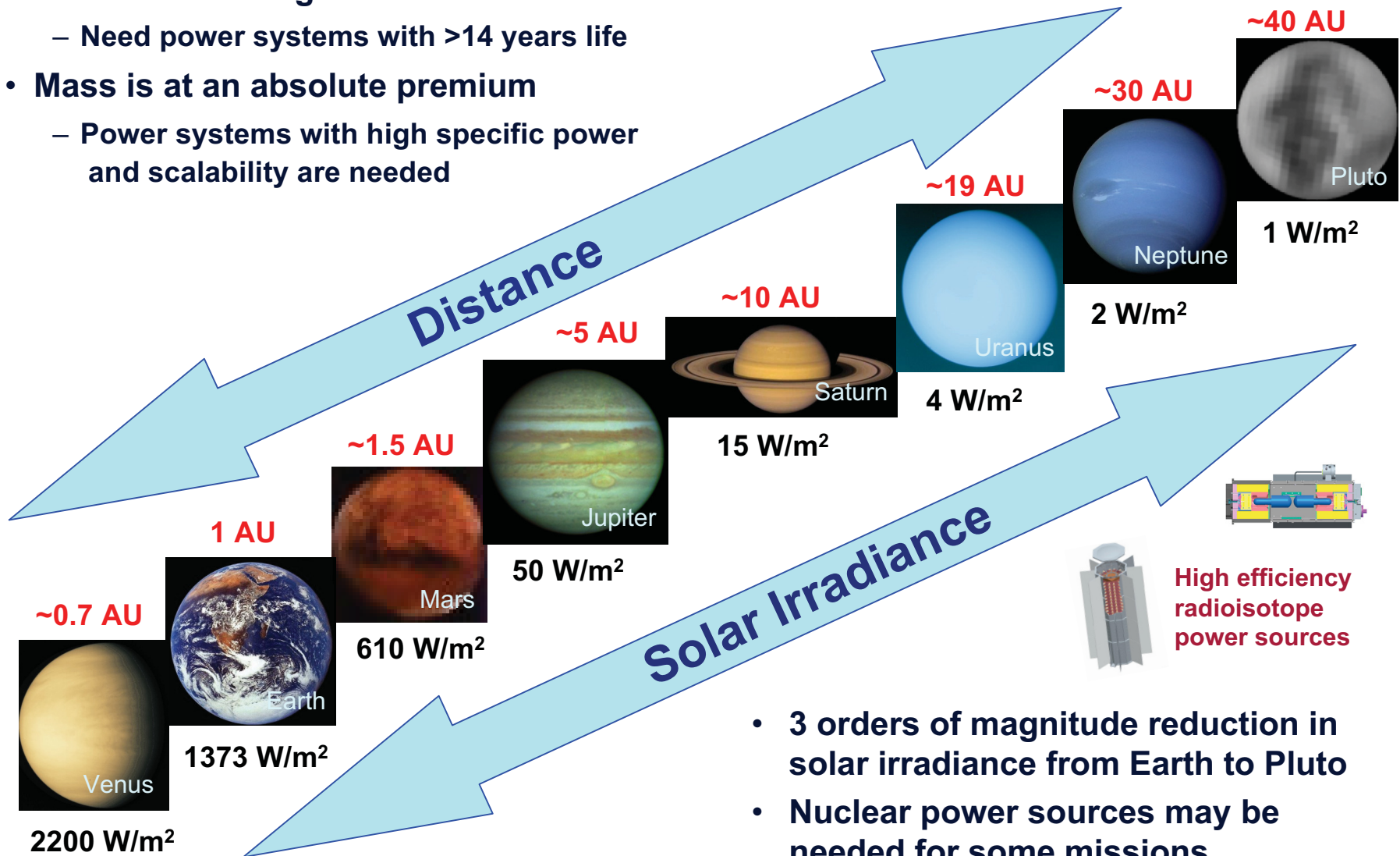




Space Power Technology



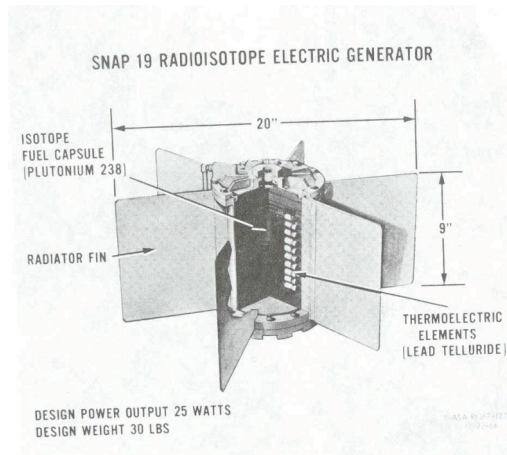
- Missions are long
 - Need power systems with >14 years life
- Mass is at an absolute premium
 - Power systems with high specific power and scalability are needed



- 3 orders of magnitude reduction in solar irradiance from Earth to Pluto
- Nuclear power sources may be needed for some missions



Flight Demonstrated Radioisotope Thermoelectric Generators RTGs) (3 Most Recently Flown Designs)

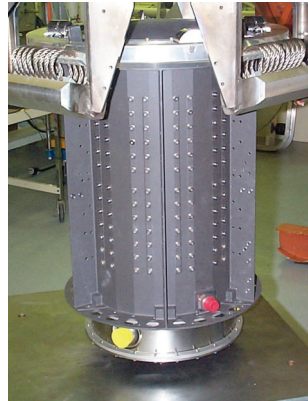


SNAP-19 (PbTe RTG)
(1960-70's)

40.3 Watts (Beginning of Mission)
6.2 % system efficiency
3 We/kg

22.86 cm (9.0 in) long
50.8 cm (20 in) diameter
~13 kg (28.6 lb)
PbTe Thermoelectrics

Nimbus B-1/III, Pioneer 10/11,
Viking 1/2

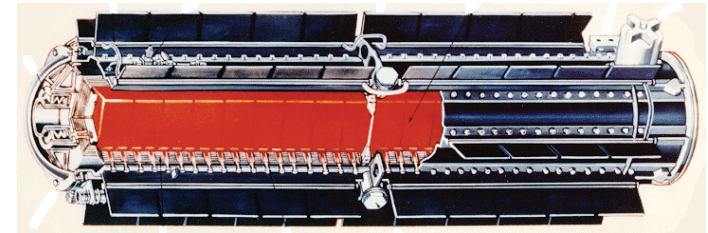


SiGe MHW RTG
(1970's)

158 We (Beginning of Mission)
6.6 % system efficiency
4.2 We/kg

58.4 cm (23 in) long
39.7 cm (15.64 in) diameter
38 kg (83.7lb)
SiGe Thermoelectrics

LES 8/9, Voyager 1/2



SiGe GPHS RTG
(1980-2006)

285 We (Beginning of Mission)
6.8% system efficiency
5.1 We/kg

114 cm (44.9 in) long
42.7cm (16.8in) diameter
56 kg (123 lb)
SiGe Thermoelectrics

Galileo, Ulysses, Cassini
& New Horizons



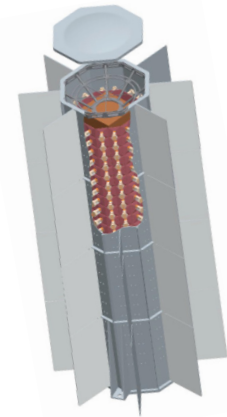
NASA Proposed Advanced RTG Needs



	Near Term	Long Term
Specific Power (W/kg)	6 - 8	> 10
Readiness	2015 - 2016	> 2020
Lifetime	> 14 years < 22% degradation	> 14 years < 22% degradation
Heat Source	Step 2 GPHS (8 to 12 units)	Step 2 GPHS (1 to 12 units)
System Efficiency (%)	8-10	13 - 15

• Advanced RTGs

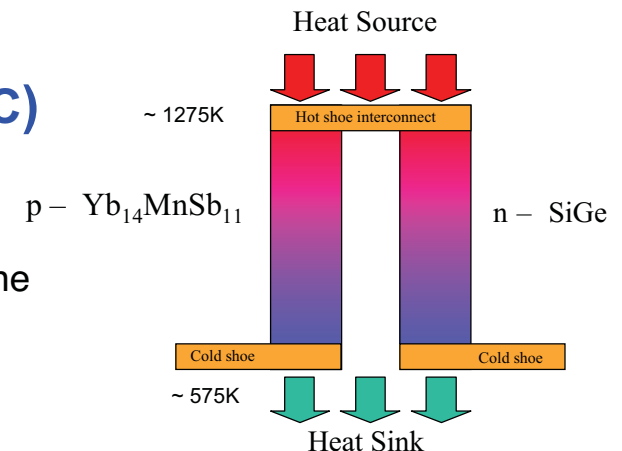
- Would require use of advanced TE materials to achieve higher efficiency
- Advanced design to improve thermal efficiency



ARTG Conceptual Design

• Advanced Thermoelectric Converter Project (ATEC)

- Developed ARTG Conceptual designs
 - Unsegmented unicouple chosen
 - Vacuum only design similar to GPHS-RTG selected as baseline
 - 6-8 W/kg
 - 8-10 % system efficiency



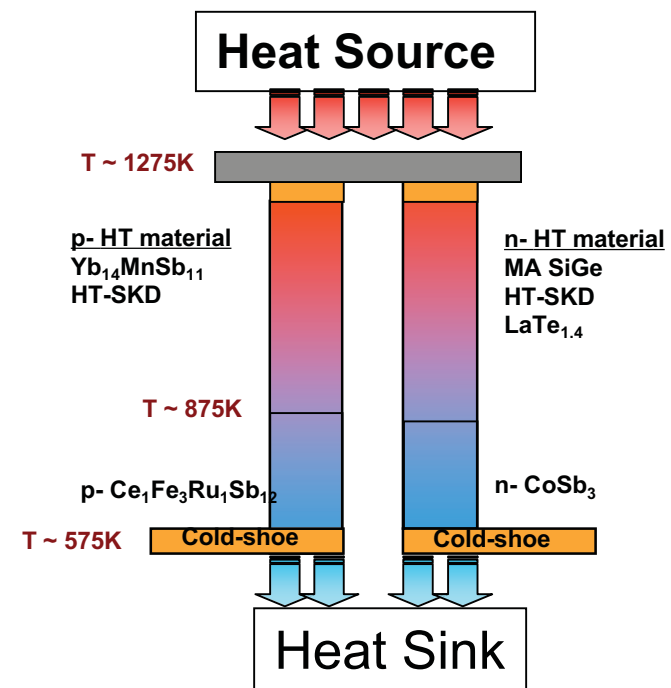
ATEC Primary unicouple configuration



ATEC Thermoelectric Materials Background



- **TE materials initially evaluated under ATEC**
 - **P-type**
 - $\text{Yb}_{14}\text{MnSb}_{11}$ (Zintl)
 - HT-Skutterudite: $\text{Ce}_y\text{Ru}_{1-x}\text{Fe}_x\text{Sb}_{12}$
 - $\text{CeFe}_3\text{Ru}_1\text{Sb}_{12}$
 - Nanostructured SiGe
 - **N-type**
 - Mechanically alloyed SiGe
 - $\text{LaTe}_{1.4}$
 - CoSb_3
 - HT-Skutterudite: $\text{Co}_x\text{Ir}_{1-x}\text{Sb}_3$
- **TE materials requirements**
 - Must be phase stable at maximum operating temperature
 - Can be produced by a synthesis process that is scalable
 - Must have repeatable thermoelectric properties

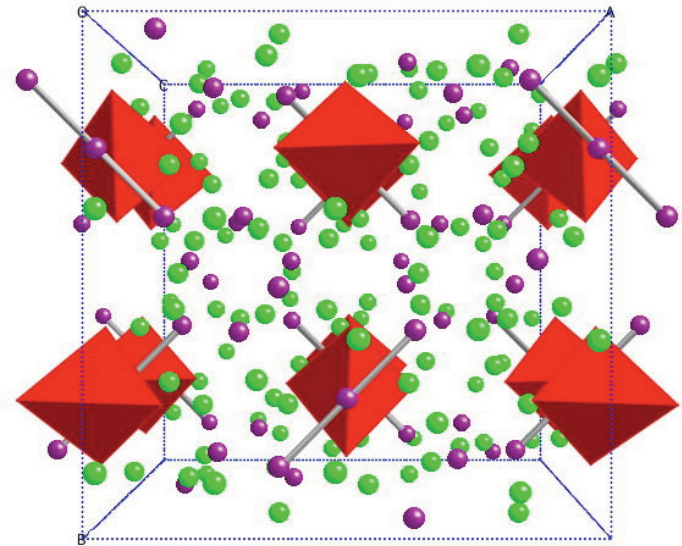




Zintl Compounds for Thermoelectric Applications



- **$A_{14}MSb_{11}$ Zintl compounds**
 - A: Ca, Sr, Yb, Eu ...
 - M: Al, In, Ga, Mn, Zn ...
 - Many opportunities for doping and disorder
 - High decomposition temperatures $>1275K$
- **$Yb_{14}MnSb_{11}$**
 - High ZT reported¹
 - Samples prepared by a flux method, milled, and hot-pressed
 - ZT ~ 1 at 1223K
 - Decomposition temperature $> 1275K$
- **$Ca_{14}AlSb_{11}$**
 - Ca^{2+} and Al^{3+}
 - Electron balanced
- **$Yb_{14}MnSb_{11}$**
 - XPS $\rightarrow Yb^{2+}$ but Mn^{2+}
 - Electron deficient \rightarrow p-type behavior expected







¹ S. Brown *et al.*, *Chem. Mat.*, 18, 1873 (2006)



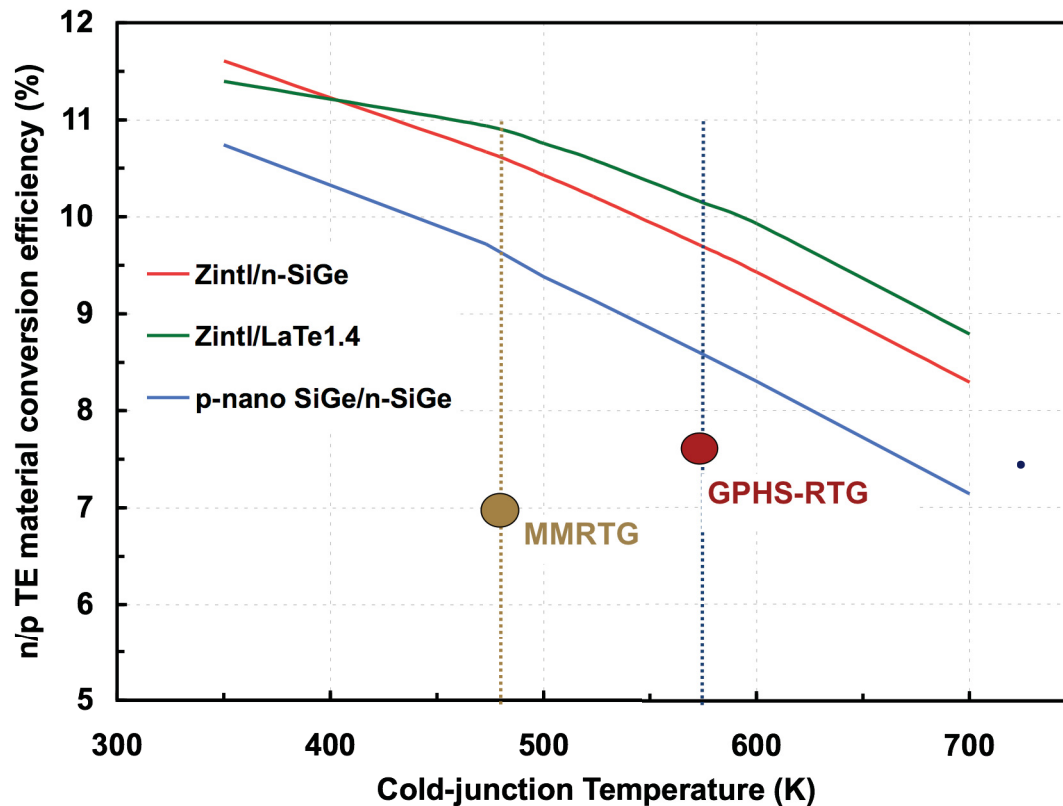
Thermoelectric materials development status



Status			Decomposition temperature (K)	ZT _{ave} (1275 K - 575K)	TE properties repeatability demonstrated	Scaled-up synthesis process (100 g batch)
Primary p-type		P-Zintl (Yb ₁₄ MnSb ₁₁)	≥ 1523	0.81	Yes	Developed
		P-nano SiGe	~ 1553	0.56	Yes	Feasibility demonstrated
Back-up p-type		P-low T SKD	~ 1050K	-	Yes	Developed
		P-high T SKD	≥ 1275K	-	No	Not developed
Primary n-type		N- SiGe	~1553	0.75	Yes	Developed
		N-LaTe _{1.4}	≥ 1523	0.88	No	Feasibility demonstrated
Back-up n-type		N-low T SKD	~ 1050K	-	Yes	Developed
		P-high T SKD	≥ 1275K	-	No	Not developed



Couple configuration options selected



- Preliminary ARTG conceptual system design and performance studies
 - Conducted by DOE contractors
 - Showed that several high-T materials combination can yield system efficiency ~ 10% and specific power greater than 6 W/kg
 - Segmenting high-T materials to low-temperature skutterudite materials does not provide substantial increase in efficiency (~0.5%) but adds development risk
 - Segmented configuration (with skutterudites) was not retained for further development
- High-T couple configurations selected for development :
 - Primary
 - P-type Yb₁₄MnSb₁₁ (Zintl)
 - N-type mechanically alloyed SiGe
 - Back-ups
 - N-LaTe_{1.4}
 - P-type Yb₁₄MnSb₁₁ (Zintl)
 - N-type mechanically alloyed SiGe
 - P-nano SiGe

- **Power metallurgy synthesis**

- Melting of elements up to ~ 1475 K in various crucibles under vacuum
- Various post-anneal and milling steps
- Milling in steel or WC under inert atmosphere
- End product: powder



- **Planetary ball milling**

- Vial load capacity: up to 250 g
- Steel vials and balls
- End product: powder



- **Vibratory ball milling**

- Vial load capacity 10 – 15g
- WC or steel vials and balls
- End product: powder



- **Electrical resistivity (ρ)** - up to ~ 1375 K
 - Van der Pauw
 - ~ 1 mm thick x 12 mm diameter disk
 - Error $\sim 2\%$
- **Seebeck coefficient (α)** - up to ~ 1375 K
 - Small gradient technique
 - ~ 1 mm thick x 12 mm diameter disk
 - Error $\sim 5\%$



High-temperature Hall effect and van der Pauw measurement system



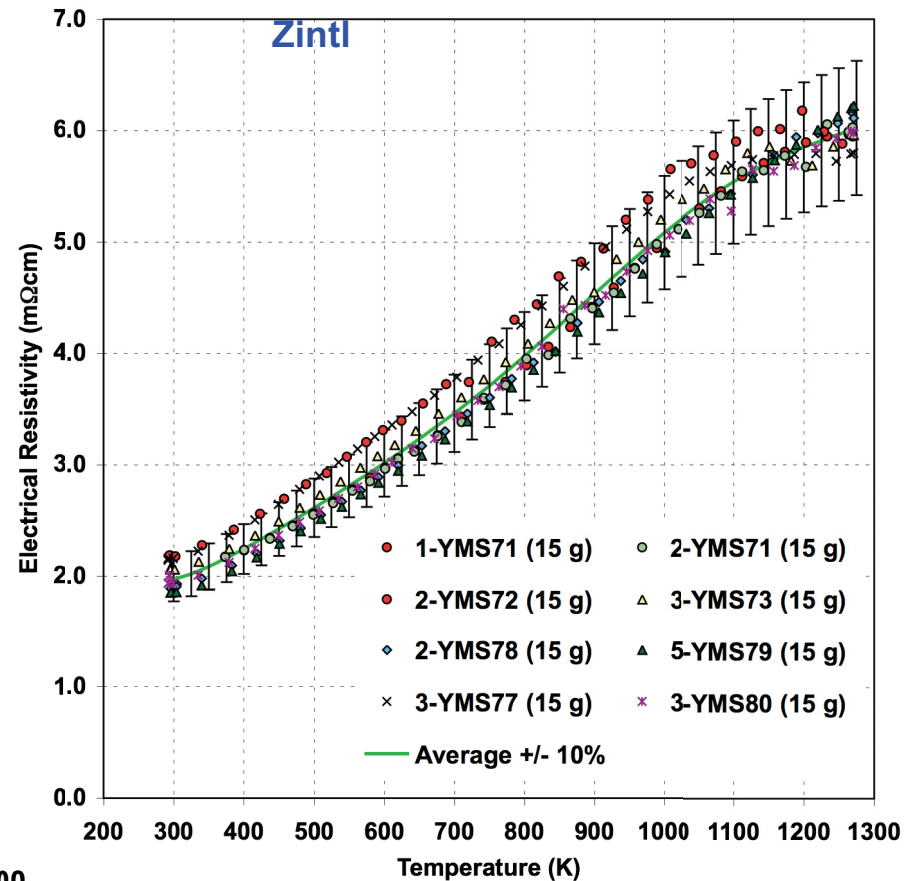
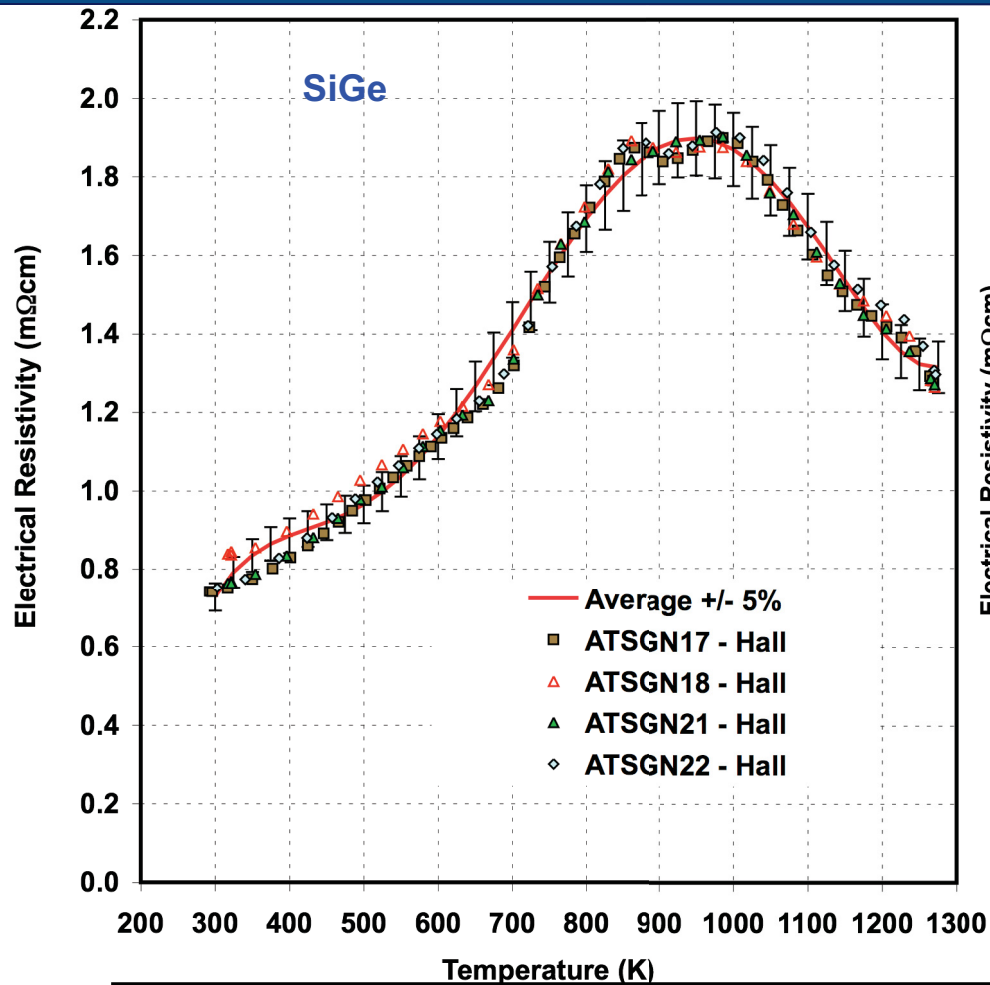
Laser flash diffusivity system used for thermal conductivity measurements

$$ZT \sim \frac{\alpha^2}{\rho\lambda} T$$

- **Thermal conductivity (λ)** - up to ~ 1375 K
 - Laser flash LFA 457- Diffusivity
 - Heat capacity measured - DSC
 - Use measured geometric density
 - ~ 1 mm thick x 12 mm diameter disk
 - Error $\sim 10\%$



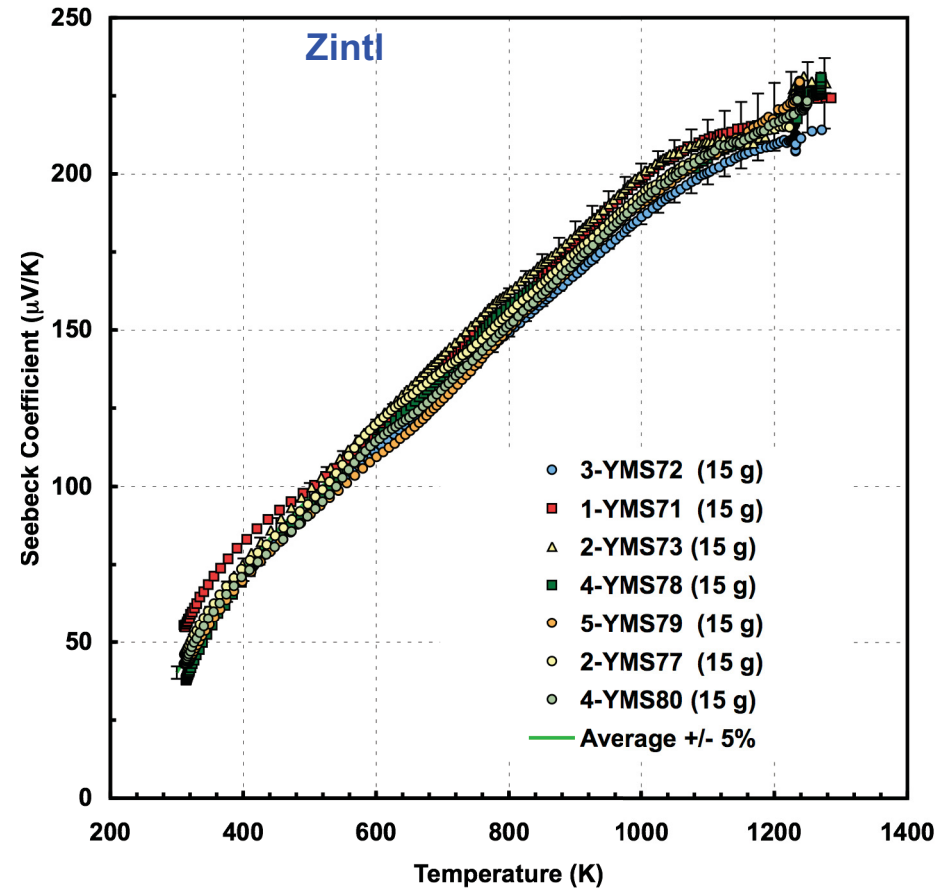
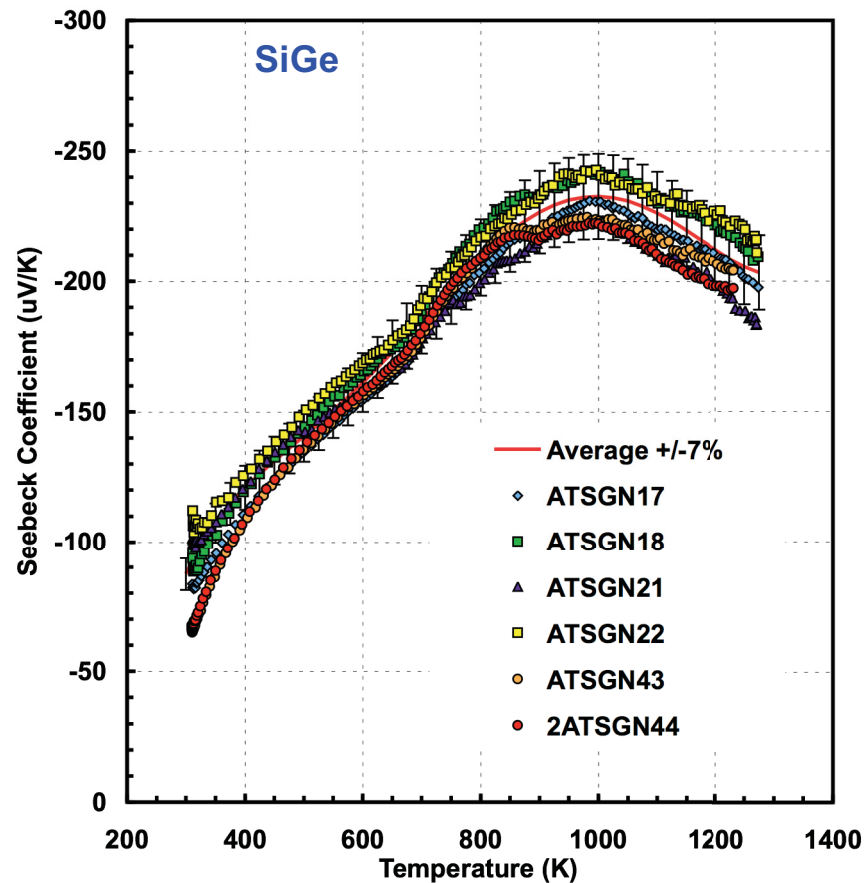
Electrical resistivity (SiGe - Zintl)



Established repeatability of electrical resistivity for a minimum of four 15 g batches of Zintl and n-MA SiGe



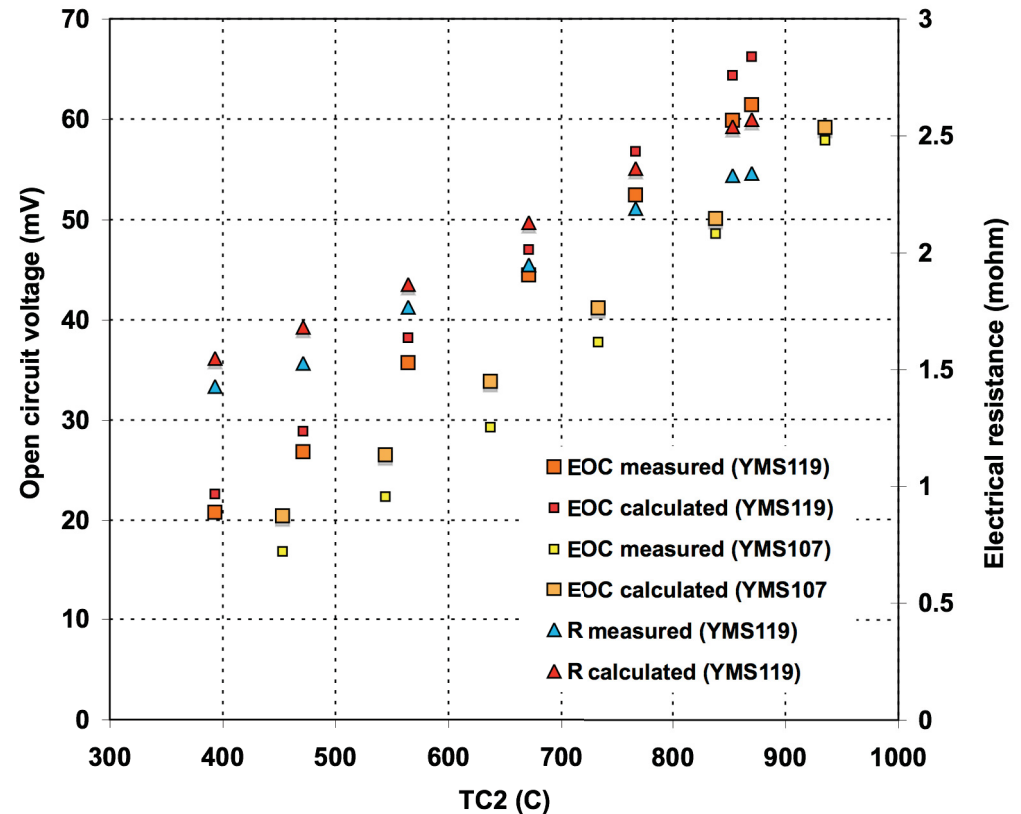
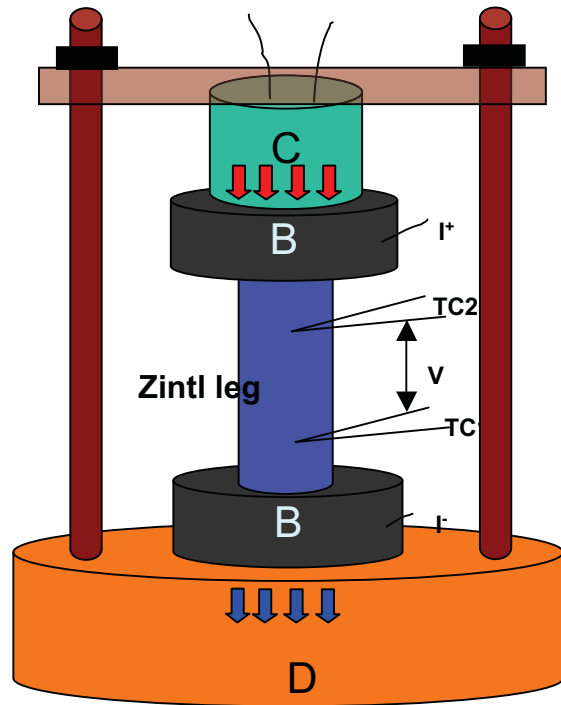
Seebeck coefficient (SiGe- Zintl)



Established repeatability of Seebeck coefficient for a minimum of four 15 g batches of Zintl and n-MA SiGe



Seebeck and resistivity - In-gradient validation JPL



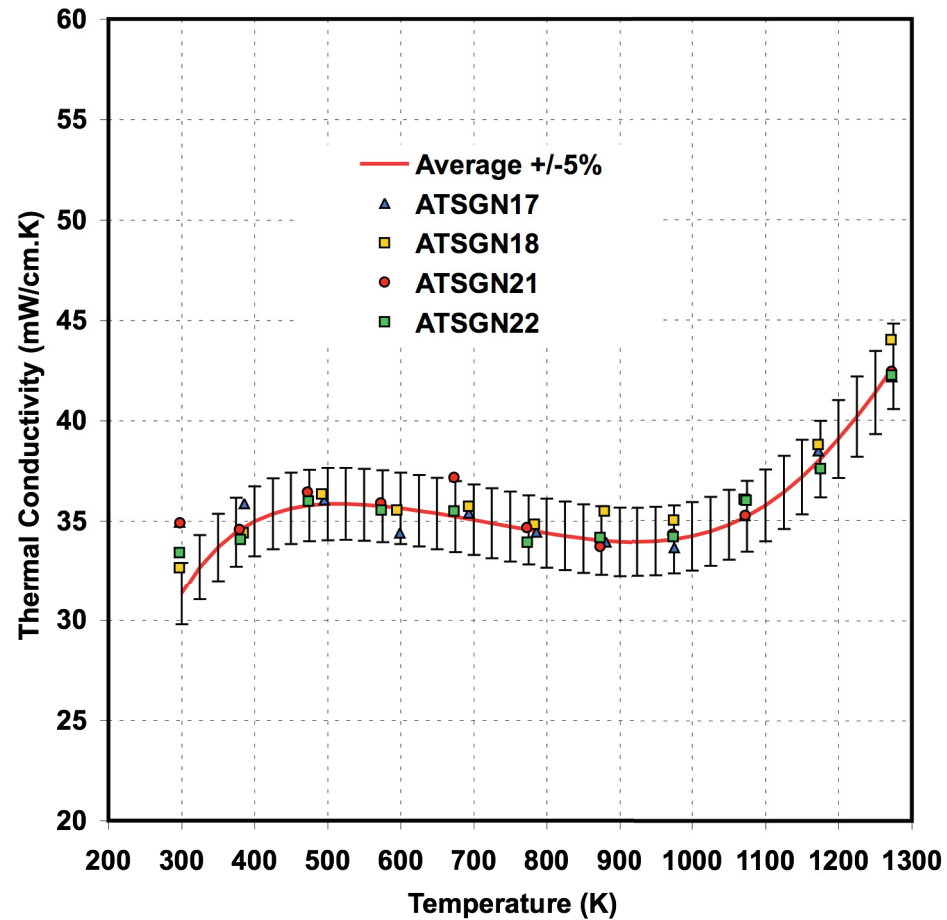
- **In-gradient validation of electrical resistivity and Seebeck coefficient**
 - Zintl leg subjected to large temperature gradient (up to 500 K) in vacuum
 - Measuring voltage and temperature using TC1 and TC2
- **Good agreement between measured voltage and electrical resistance and calculated voltage and resistance from measured Seebeck and electrical resistivity values**



Thermal conductivity (SiGe)



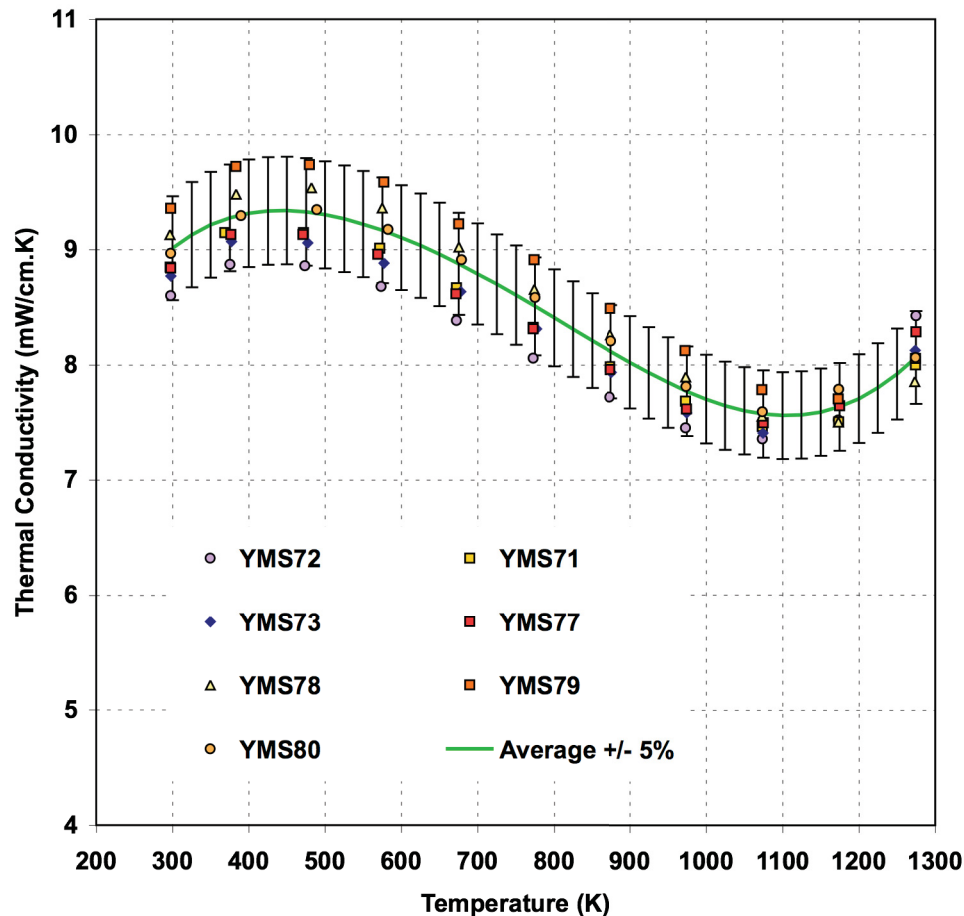
SiGe



Established repeatability of thermal conductivity for a minimum of four 15 g batches of n-MA SiGe



Thermal conductivity (Zintl)



$$\lambda_L = \frac{B M \bar{\delta} \theta^2}{q^{2/3} \gamma^2} \quad \gamma = 3 \alpha K V_m / C_v$$

- **Low thermal conductivity**

- Consistent with previous measurement

- **Calculated lattice thermal conductivity (Wiedemann-Franz)** $\lambda = \lambda_L + L \sigma T$

- Average value = 6.1 mW/cmK

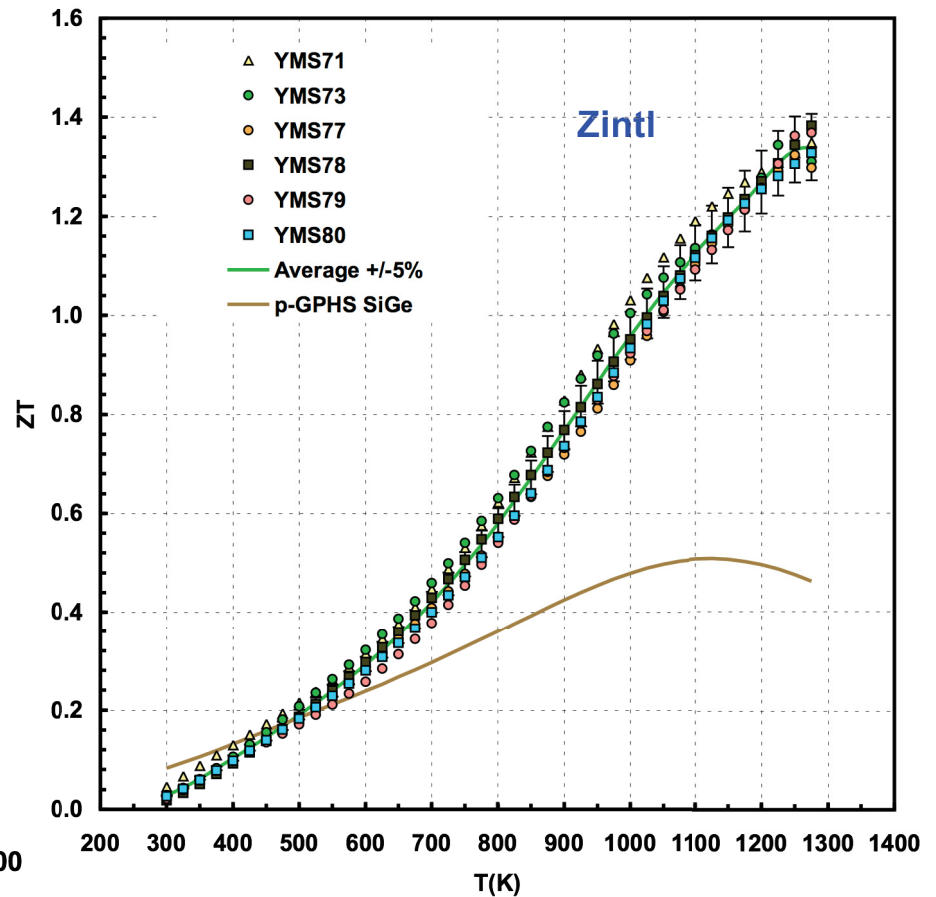
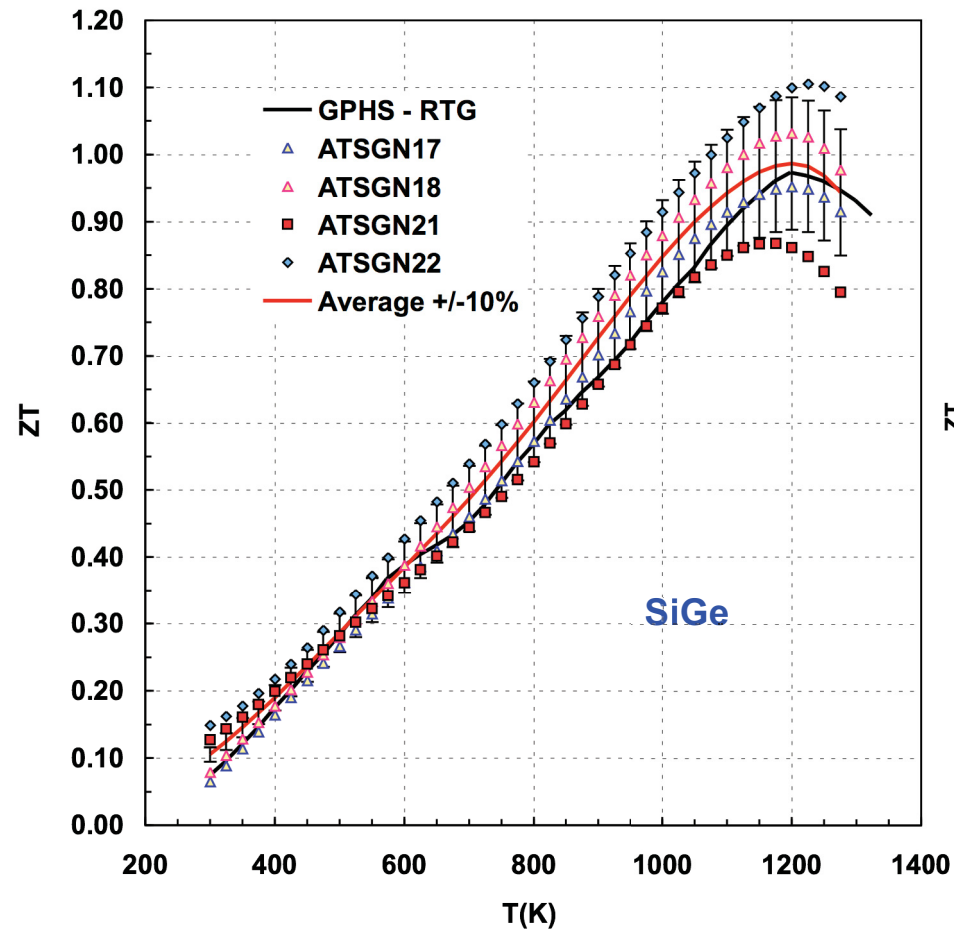
- **Calculated lattice thermal conductivity (Slack)**

- 5.1 mW/cmK

- **M** = molecular weight
- **B** = $3.04 \times 10^7 \text{ s}^{-3} \text{ K}^{-3}$
- **q** = number of atoms per molecule
- **γ** = Grüneisen constant
- **V_m** = averaged sound velocity
- **α** = linear coefficient of expansion
- **C_v** = specific heat capacity per mole



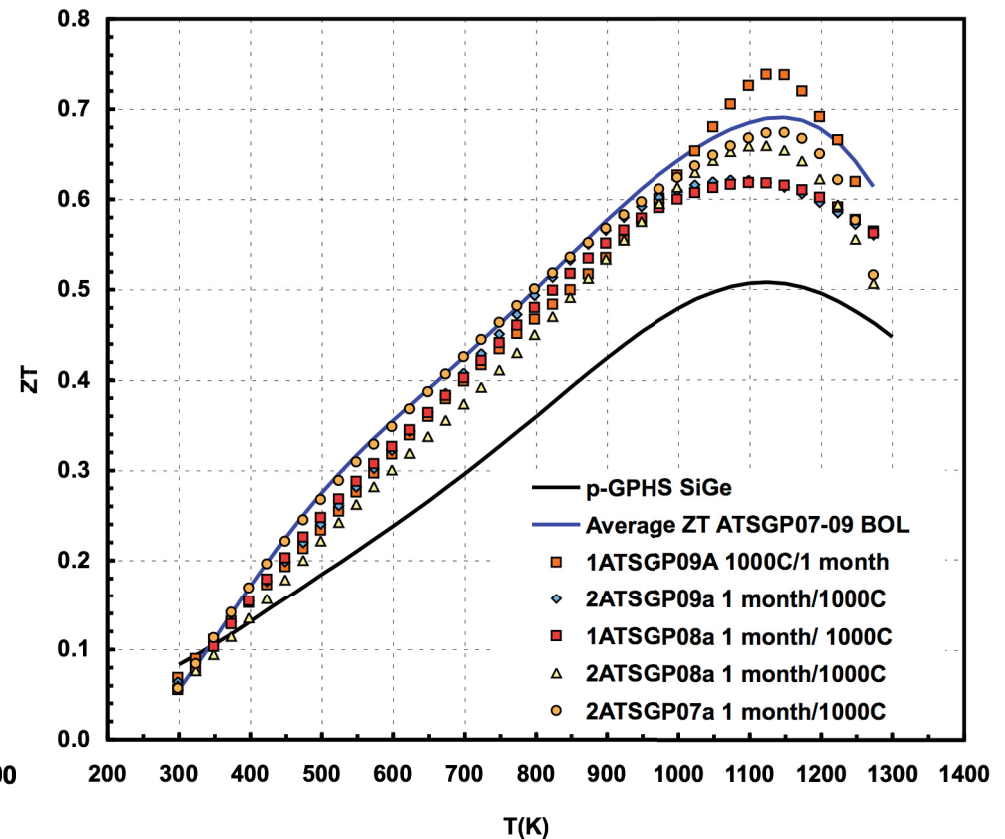
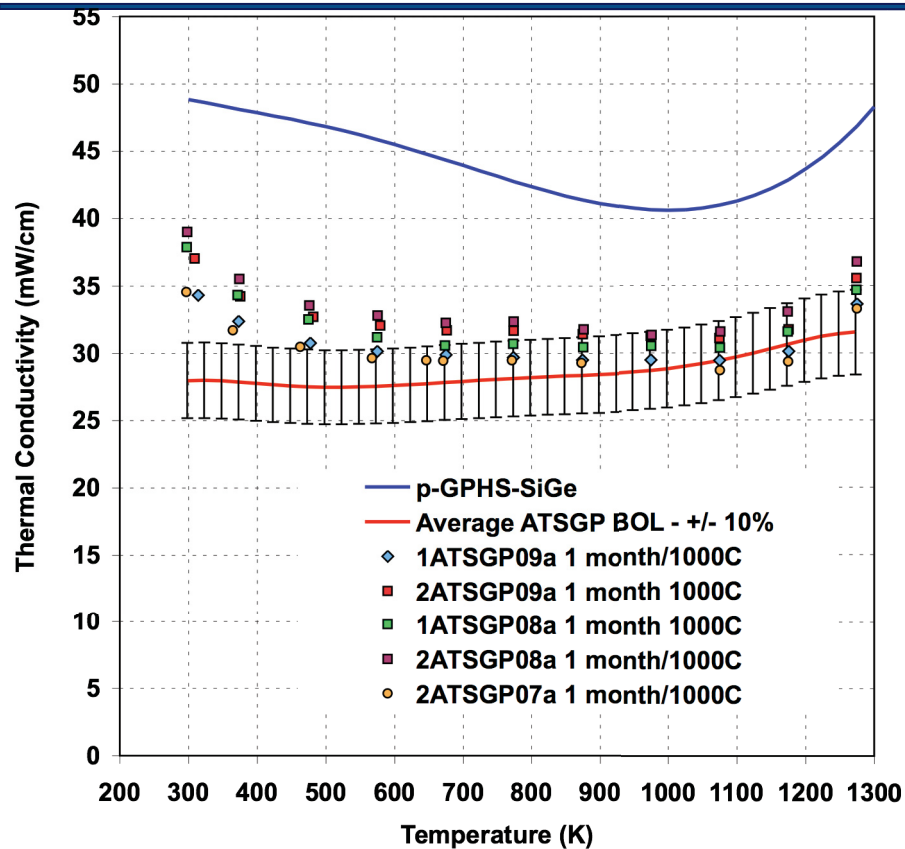
ZT (SiGe- Zintl)



Established repeatability of ZT for a minimum of four 15 g batches of Zintl and n-MA SiGe



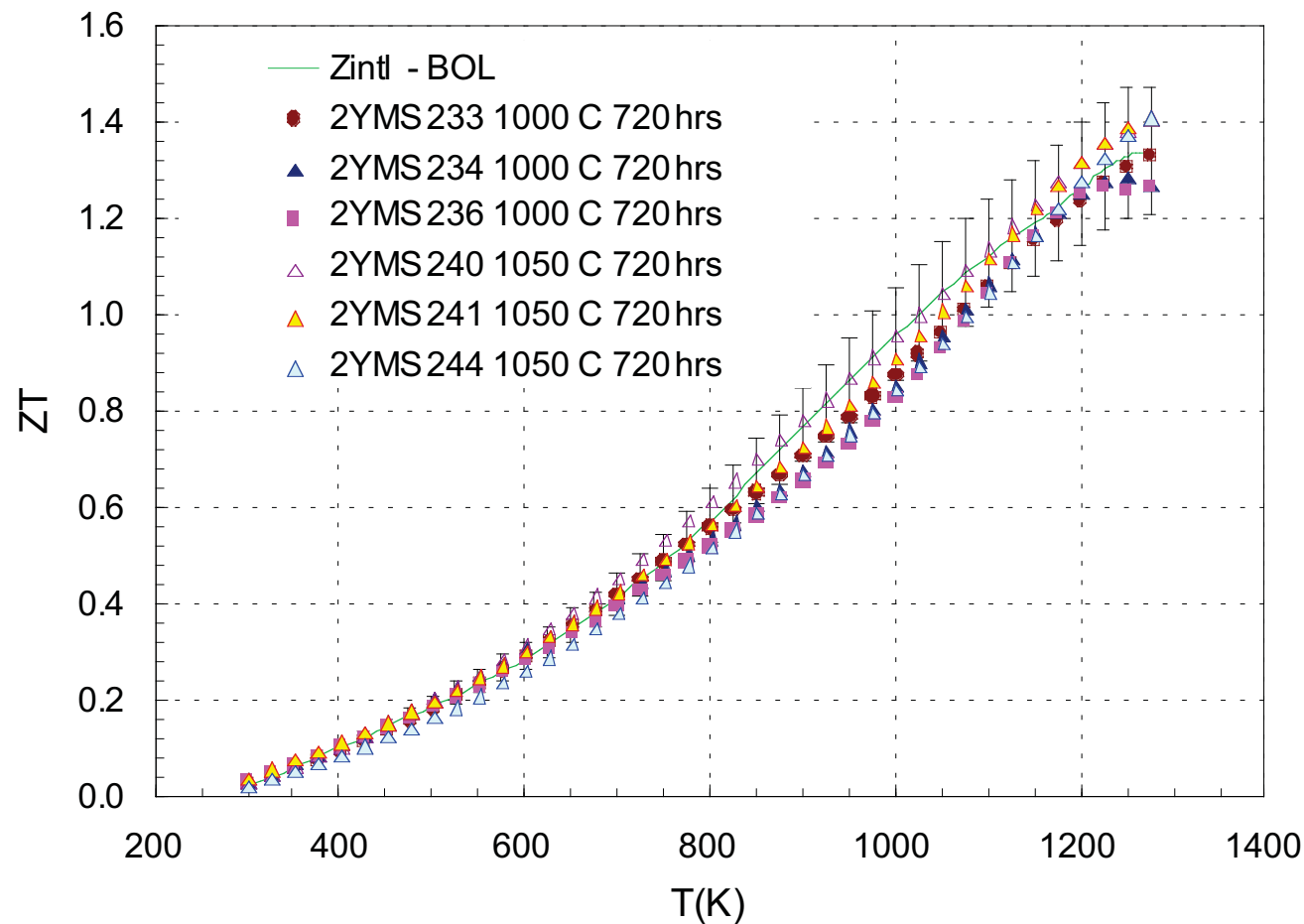
Thermal conductivity and ZT values for p-nano SiGe



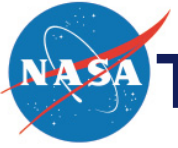
- ZT values after 1 month anneal at 1275K show ~ 30% improvement over p-GPHS SiGe
- Relatively small increase in thermal conductivity after anneal



Zintl TE properties life testing



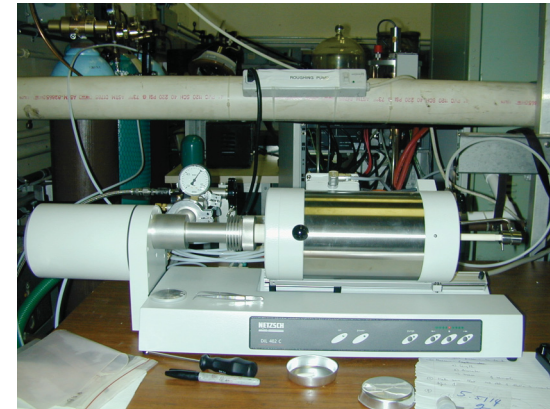
**Post anneal ZT values for four different batches
are within $\pm 10\%$ of BOL values**



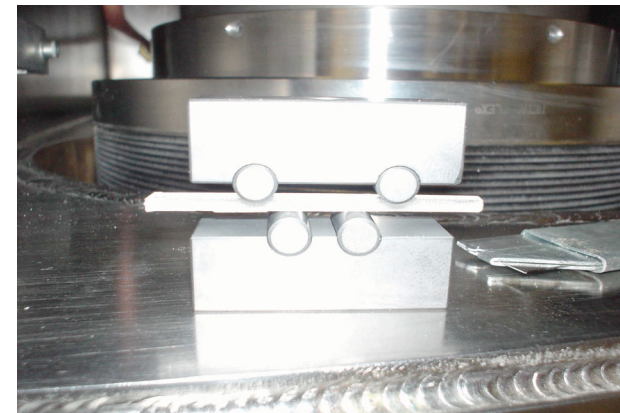
TE materials thermo-mechanical properties



- **Mechanical properties data essential for:**
 - Process development (loading and bonding pressures, etc)
 - Mechanical integrity (handling issues, manufacturing, launch stresses, long-term high temperature performance, residual stresses)
- **Properties of interest**
 - **Stiffness**
 - Elastic Moduli (Young's, shear, bulk, flexural)
 - Poisson's ratio (strain ratio in elastic regime)
 - **Strength**
 - Ultimate load that the material can handle
 - Flexure, compression
 - **Toughness**
 - Resistance to crack propagation
 - fracture toughness
 - Critical in assessing if the material is susceptible to sudden, brittle fracture (low values of fracture toughness)
 - **Coefficient of thermal expansion**
 - Key in determining mechanical stress state at interfaces of multilayer stack



High-temperature dilatometer



Bend test



Room temperature thermo-mechanical properties



	Melting or Decomposition temperature (K)	Density (g/cm ³)	Dynamic Young's Modulus, E (GPa)	Dynamic Shear Modulus, G (GPa)	Poisson's Ratio	Flexural Modulus (GPa)	Flexural Strength (MPa)	Fracture Toughness (MPa-m ^{1/2})	Average CTE (ppm/K)
P-SKD	1098	7.92	133	54	0.22 – 0.29	~ 93	~ 37	~ 2.9 *	13.5 (473 – 873 K range)
N-SKD	1049	7.61	136	60	~ 0.14 * 0.25***	~ 102	~ 86	1.6 *	11.0 (473 – 873 K range)
P-Zintl	> 1523	8.36	66***	26***	0.265***	100**	75**	1.0**	17.0 -20.0 (303 – 1273 K range)
LaTe_{1.43}	~ 1773	6.68	62***	25***	0.243**	100**	75**	1.0**	17.0 (303 – 1273 K range)
N-SiGe (ATEC)	1573	2.93	145	54**	0.25**	100**	75**	3.3*	5.0 (303 – 1273 K range)
N-SiGe (RTG)	1573	2.99				145	129	~ 0.8	~ 4.9 @ ~ 1200 K ~ 4.7 @ ~ 900 K
P-SiGe (RTG)	1573	2.99				137	201	~ 1	~ 4.8 @ ~ 1200 K ~ 4.6 @ ~ 900 K

* Preliminary Data ** Estimated (not measured) *** Calculated from speed of sound data



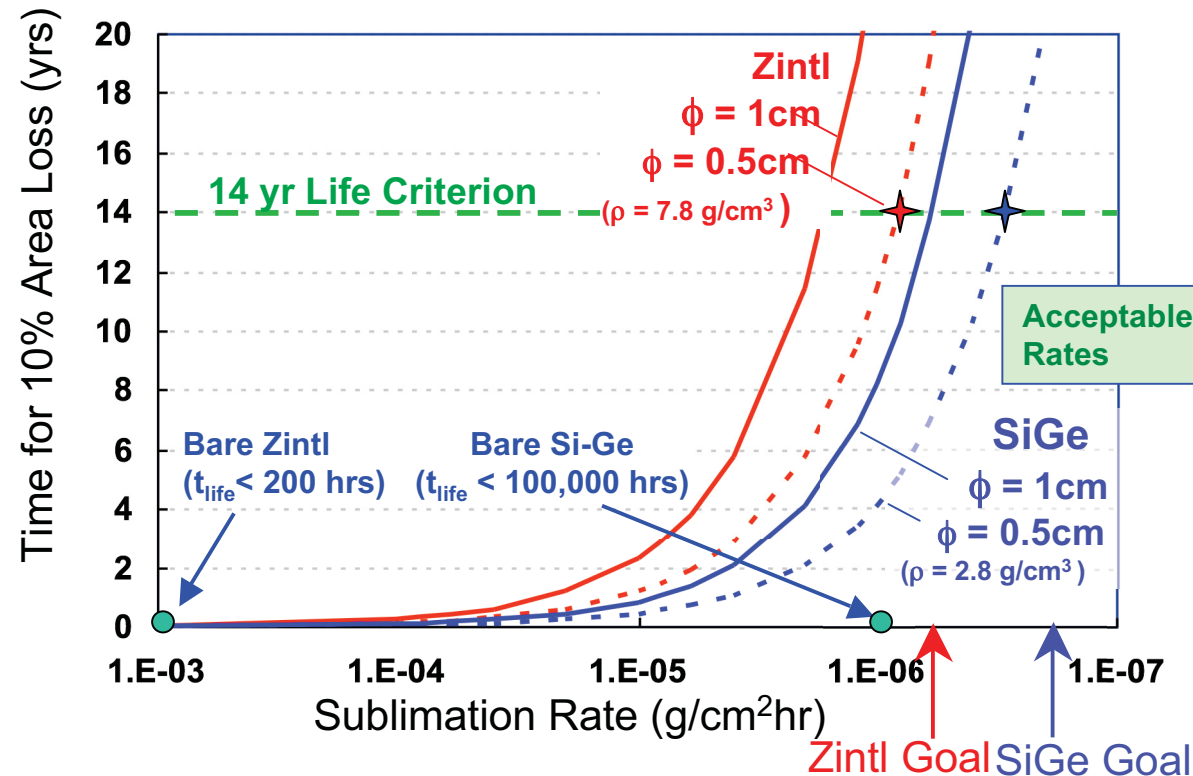
Sublimation Rates



ATEC Sublimation Suppression Requirement:

- Less than 10% cross-sectional area lost to sublimation over 14 yrs

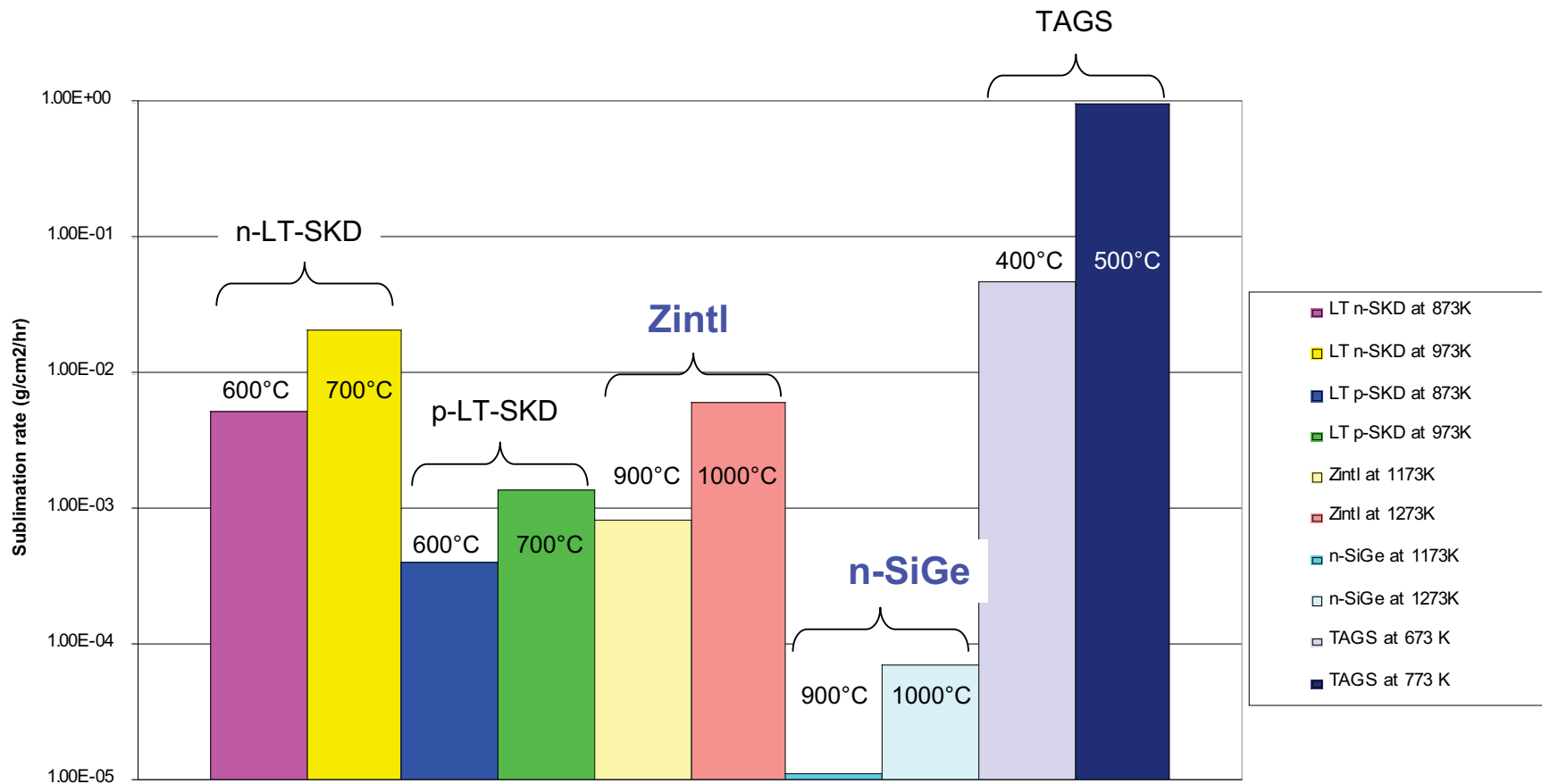
Theoretical Predictions of the Time to Lose 10% of the Cross-Sectional Area of a TE Leg



- Sublimation suppression goal for Zintl at 1275 K is $\sim 5 \times 10^{-7} \text{ g/cm}^2/\text{hr}$.
- Sublimation suppression goal for SiGe at 1275 K is $\sim 2 \times 10^{-7} \text{ g/cm}^2/\text{hr}$.



Baseline sublimation rates measured with TGA (2hrs)





Sublimation Control Development



- **Demonstrated sublimation suppression of LT-SKD with aerogel**
($\sim 5 \times 10^{-7}$ g/cm²h at 875 K for 6000 hrs).
- **Identified candidates for Zintl sublimation suppression.**
 - Ceramic cements ($\sim 100\mu\text{m}$) (Rate $\sim 5 \times 10^{-6}$ g/cm²/hr, 4 wks at 1275 K).
 - Physical barrier (no measurable sublimation during in-gradient test of Zintl leg, 1 wk at 1275 K).
 - Thin metal coatings, semi-protective after 2 wks at 1275 K.
- **Identified candidates for SiGe sublimation suppression.**
 - Graphite aerogel (Rate $\sim 8.5 \times 10^{-7}$ g/cm²/hr after 2 weeks at 1275 K).
 - Si_3N_4



Summary



- **NASA and DOE are working together to develop a next generation RTG that would provide significant benefits for future NASA deep space missions**
 - Higher payload mass/reduced power system mass
 - Lower launch vehicle costs
 - Reduced plutonium usage
 - High reliability and long life capability
- **Significant progress has been made in the area of materials and component development, and system design**
 - Demonstrated material reproducibility, scalability and initial TE property stability
 - $> 6\text{W/kg}$ and $> 8\%$ system efficiency
 - Zintl / SiGe unicouples selected
- **JPL developing the next generation of advanced materials that could lead to advanced RTGs capable of up to 17% system efficiency and over 12 W/kg specific power**
 - High temperature Zintls / rare earth chalcogenides with average $ZT \sim 2$
 - Nanostructured materials engineering of high power factor Si, Ge and III-V electronic semiconductors (1275 K – 500 K)